NSN 5961-01-464-0830

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Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-464-0830 **Inclosure Material:** Glass **Overall Length:** 7.490 millimeters **Terminal Length:** 5.970 millimeters **Overall Width:** 2.190 millimeters **End Application:** 6625-01-443-0552 **Mounting Facility Quantity: Mounting Method: Terminal Semiconductor Material:** Silicon **Voltage Rating In Volts Per Characteristic:** 60.0 breakdown voltage, collector to emitter, sustained and 60.0 breakdown voltage, collector-to-base, emitter open **Current Rating Per Characteristic:** 5.00 milliamperes source cutoff current **Power Rating Per Characteristic:** 10.0 watts small-signal output power, common-base preset **Maximum Operating Tempurature Per Measurement Point:** -55.0 degrees celsius case and 150.0 degrees celsius case **Special Features:** Low-frequency power silicon pnp bjt **Terminal Type And Quantity:** 3 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** No